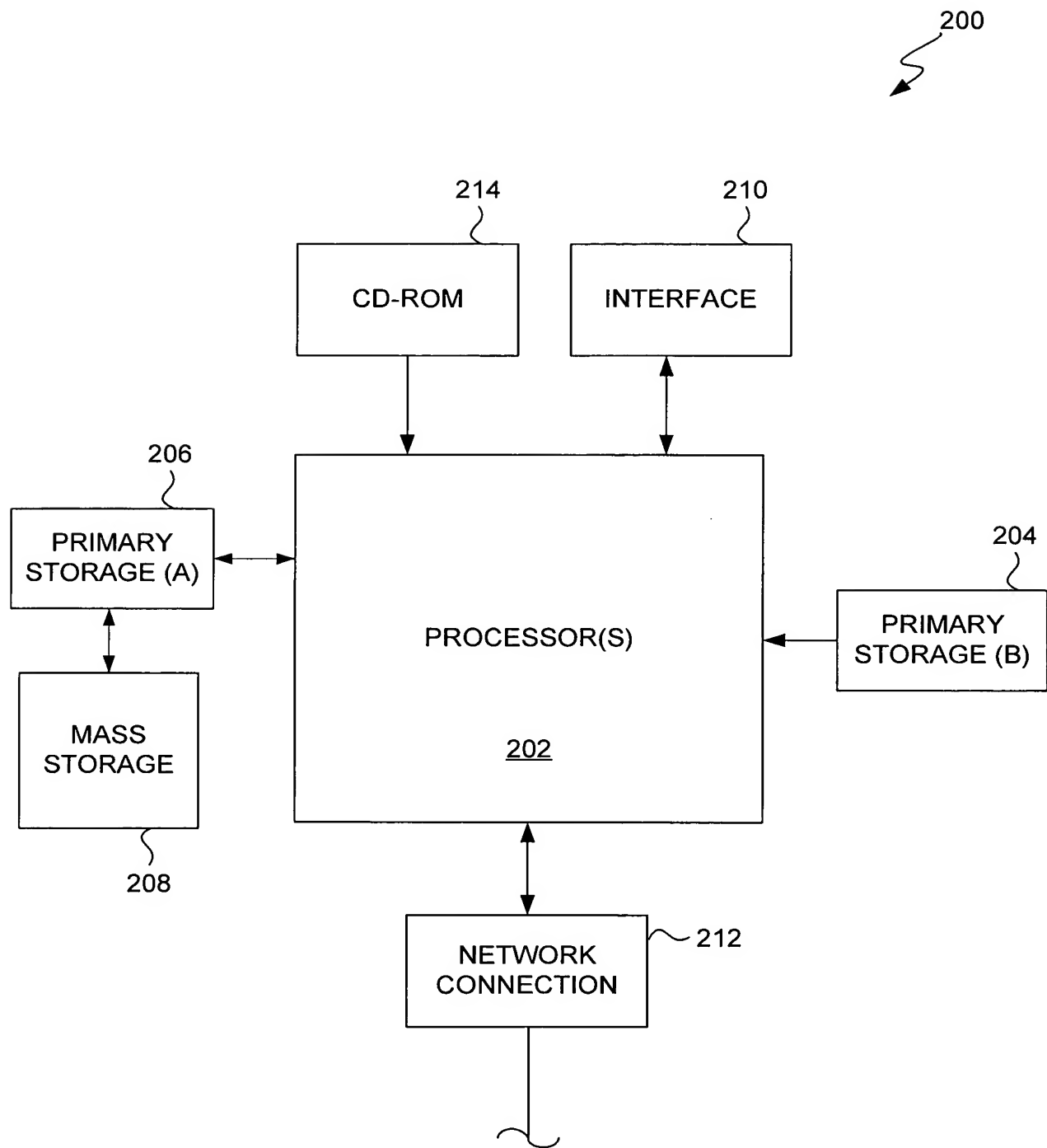
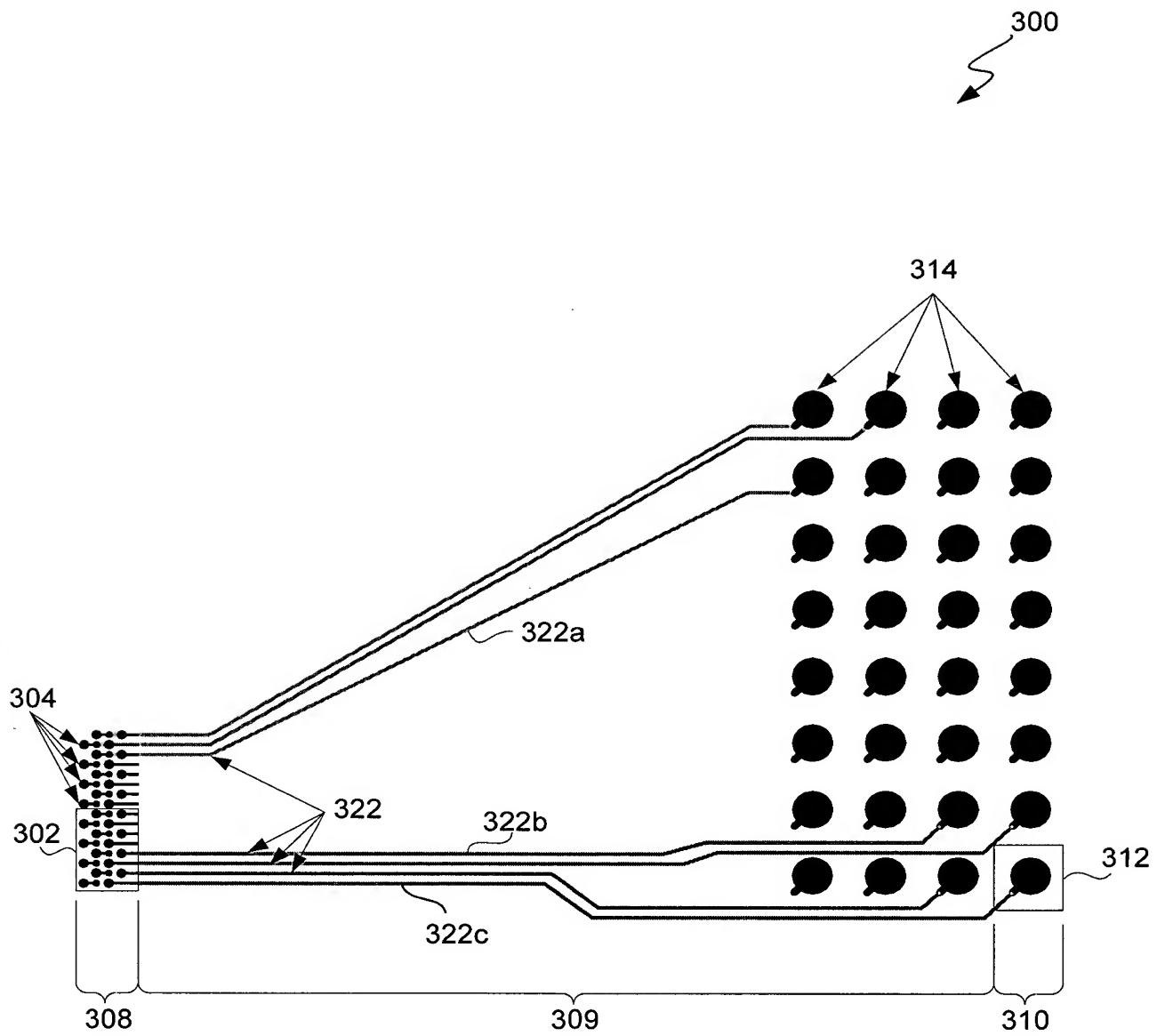


A cross-sectional view of a semiconductor device 100. The device is built on a substrate 116. A layer 110 is formed on the substrate, containing a series of circular features 114. Above layer 110 is a layer 120, which contains a series of circular features 118. The features 118 are divided into three groups: 118a, 118b, and 118c. A layer 104 is formed on top of layer 120. A layer 102 is formed on top of layer 104. A layer 106 is formed on top of layer 102. A layer 108 is formed on top of layer 106. A layer 122a is formed on top of layer 108. A layer 122b is formed on top of layer 122a. A layer 124 is formed on top of layer 122b. A layer 126 is formed on top of layer 124. A layer 130 is formed on top of layer 126. A layer 132 is formed on top of layer 130. A layer 134 is formed on top of layer 132. A layer 128 is formed on top of layer 134. A layer 112 is formed on top of layer 128. A layer 114 is formed on top of layer 112.

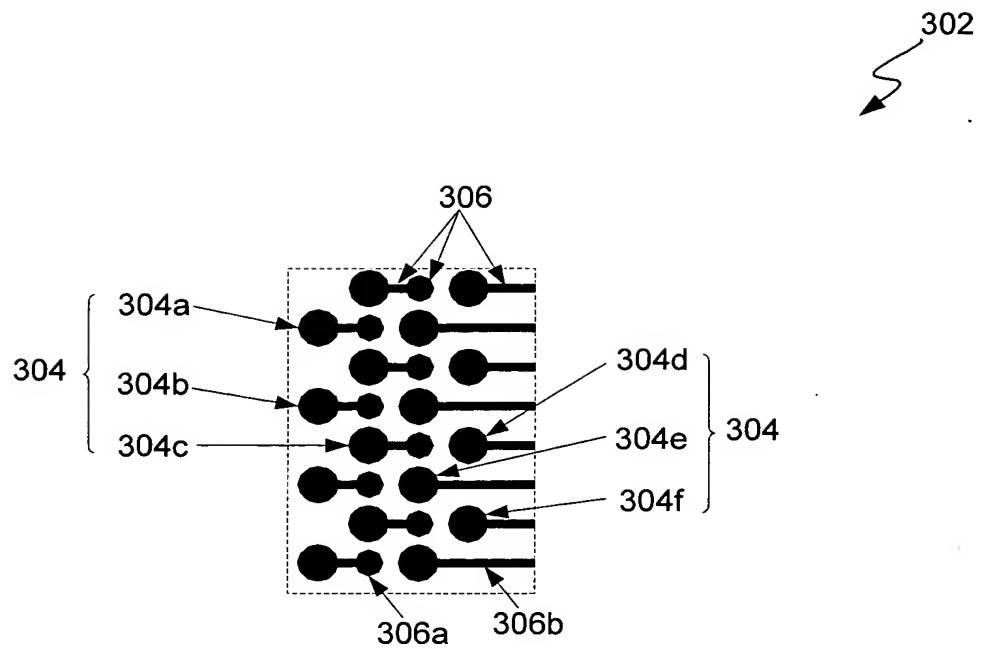
**FIG. 1**



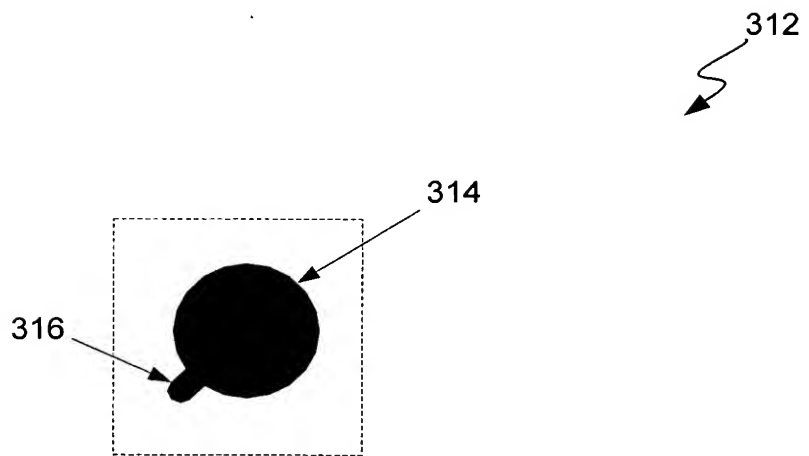
**FIG. 2**



**FIG. 3A**

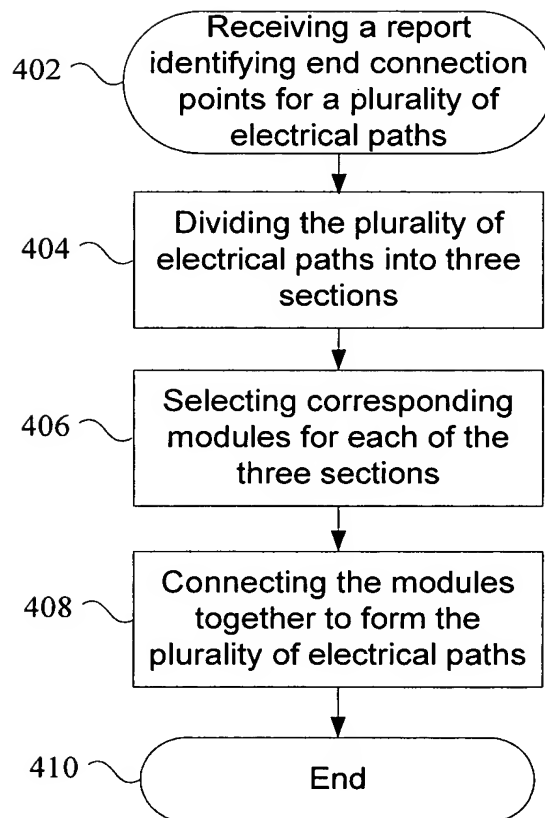


**FIG. 3B**



**FIG. 3C**

400



**FIG. 4**